

ZHEN
Serial No. 09/842,631



VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

27. {AMENDED} A semiconductor device fabricating method as claimed in claim 25 [or 26], wherein

the ferroelectric thin film is made of a material expressed by:



where A represents one selected from a group consisting of Na, K, Pb, Ca, Sr, Ba and Bi,

B represents one selected from a group consisting of Fe, Ti, Nb, Ta, W and Mo, and m represents a natural number.

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